

Fernando A. Ponce

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330
papers

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357
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ext. citations

3.2
avg, IF

5.89
L-index

#	Paper	IF	Citations
330	Nitride-based semiconductors for blue and green light-emitting devices. <i>Nature</i> , 1997 , 386, 351-359	50.4	1389
329	High dislocation densities in high efficiency GaN-based light-emitting diodes. <i>Applied Physics Letters</i> , 1995 , 66, 1249-1251	3.4	853
328	Defects in single-crystal silicon induced by hydrogenation. <i>Physical Review B</i> , 1987 , 35, 4166-4169	3.3	400
327	Spatial distribution of the luminescence in GaN thin films. <i>Applied Physics Letters</i> , 1996 , 68, 57-59	3.4	329
326	Luminescence from stacking faults in gallium nitride. <i>Applied Physics Letters</i> , 2005 , 86, 021908	3.4	301
325	Self-limiting oxidation for fabricating sub-5 nm silicon nanowires. <i>Applied Physics Letters</i> , 1994 , 64, 1383-1385	3.4	233
324	Determination of lattice polarity for growth of GaN bulk single crystals and epitaxial layers. <i>Applied Physics Letters</i> , 1996 , 69, 337-339	3.4	216
323	Epitaxial MgO on Si(001) for Y-Ba-Cu-O thin-film growth by pulsed laser deposition. <i>Applied Physics Letters</i> , 1991 , 58, 2294-2296	3.4	216
322	Edge and screw dislocations as nonradiative centers in InGaN/GaN quantum well luminescence. <i>Applied Physics Letters</i> , 2001 , 78, 2691-2693	3.4	198
321	Microstructure of GaN epitaxy on SiC using AlN buffer layers. <i>Applied Physics Letters</i> , 1995 , 67, 410-412	3.4	181
320	Slip systems and misfit dislocations in InGaN epilayers. <i>Applied Physics Letters</i> , 2003 , 83, 5187-5189	3.4	175
319	Characterization of dislocations in GaN by transmission electron diffraction and microscopy techniques. <i>Applied Physics Letters</i> , 1996 , 69, 770-772	3.4	175
318	Improvement of peak quantum efficiency and efficiency droop in III-nitride visible light-emitting diodes with an InAlN electron-blocking layer. <i>Applied Physics Letters</i> , 2010 , 96, 221105	3.4	168
317	Initial stages of epitaxial growth of GaAs on (100) silicon. <i>Journal of Applied Physics</i> , 1987 , 61, 1856-1859	2.5	143
316	Self-limiting oxidation of Si nanowires. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1993 , 11, 2532		139
315	Crystalline structure of AlGaIn epitaxy on sapphire using AlN buffer layers. <i>Applied Physics Letters</i> , 1994 , 65, 2302-2304	3.4	118
314	MOVPE growth of GaN on Si(1 1 1) substrates. <i>Journal of Crystal Growth</i> , 2003 , 248, 556-562	1.6	117

313	Microstructure and electronic properties of InGaN alloys. <i>Physica Status Solidi (B): Basic Research</i> , 2003 , 240, 273-284	1.3	115
312	Exciton freeze-out and thermally activated relaxation at local potential fluctuations in thick Al _x Ga _{1-x} N layers. <i>Journal of Applied Physics</i> , 2004 , 95, 4670-4674	2.5	108
311	Atomic arrangement at the AlN/Si (111) interface. <i>Applied Physics Letters</i> , 2003 , 83, 860-862	3.4	102
310	Metalorganic chemical vapor phase epitaxy of gallium-nitride on silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 1583-1606		101
309	Hydrogen in crystalline semiconductors. <i>Physica B: Condensed Matter</i> , 1991 , 170, 3-20	2.8	99
308	Dislocation annihilation by silicon delta-doping in GaN epitaxy on Si. <i>Applied Physics Letters</i> , 2002 , 81, 4712-4714	3.4	98
307	Homoepitaxy of GaN on polished bulk single crystals by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 1996 , 68, 917-919	3.4	98
306	Strained Ga/sub x/In/sub 1-x/P/(AlGa)/sub 0.5/In/sub 0.5/P heterostructures and quantum-well laser diodes. <i>IEEE Journal of Quantum Electronics</i> , 1994 , 30, 593-607	2	89
305	Thermodynamic and kinetic considerations on the equilibrium shape for thermally induced microdefects in Czochralski silicon. <i>Journal of Applied Physics</i> , 1986 , 59, 3255-3266	2.5	88
304	Observation of coreless dislocations in GaN. <i>Journal of Crystal Growth</i> , 1997 , 178, 201-206	1.6	83
303	Oxidation of sub-50 nm Si columns for light emission study. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1992 , 10, 2846		83
302	Reactions at the interfaces of thin films of Y-Ba-Cu- and Zr-oxides with Si substrates. <i>Journal of Applied Physics</i> , 1991 , 69, 2176-2182	2.5	81
301	Improvement of quantum efficiency by employing active-layer-friendly lattice-matched InAlN electron blocking layer in green light-emitting diodes. <i>Applied Physics Letters</i> , 2010 , 96, 101102	3.4	80
300	Ion milled tips for scanning tunneling microscopy. <i>Applied Physics Letters</i> , 1987 , 50, 696-698	3.4	80
299	Efficiency droop due to electron spill-over and limited hole injection in III-nitride visible light-emitting diodes employing lattice-matched InAlN electron blocking layers. <i>Applied Physics Letters</i> , 2012 , 101, 161110	3.4	74
298	Defects and Interfaces in GaN Epitaxy. <i>MRS Bulletin</i> , 1997 , 22, 51-57	3.2	74
297	Atomic arrangement at the AlN/SiC interface. <i>Physical Review B</i> , 1996 , 53, 7473-7478	3.3	72
296	Preparation of oriented Bi-Ca-Sr-Cu-O thin films using pulsed laser deposition. <i>Applied Physics Letters</i> , 1988 , 53, 337-339	3.4	72

295	Pulsed lateral epitaxial overgrowth of aluminum nitride on sapphire substrates. <i>Applied Physics Letters</i> , 2006 , 89, 081905	3-4	71
294	Low-threshold stimulated emission at 249 nm and 256 nm from AlGaIn-based multiple-quantum-well lasers grown on sapphire substrates. <i>Applied Physics Letters</i> , 2014 , 105, 141106	3-4	68
293	Deep-ultraviolet lasing at 243 nm from photo-pumped AlGaIn/AlN heterostructure on AlN substrate. <i>Applied Physics Letters</i> , 2013 , 102, 101110	3-4	66
292	Prismatic stacking faults in epitaxially laterally overgrown GaN. <i>Applied Physics Letters</i> , 2006 , 88, 141912	3-4	66
291	Light emission and microstructure of Mg-doped AlGaIn grown on patterned sapphire. <i>Applied Physics Letters</i> , 2003 , 82, 349-351	3-4	62
290	Structure of thermally induced microdefects in Czochralski silicon after high-temperature annealing. <i>Applied Physics Letters</i> , 1983 , 43, 1051-1053	3-4	61
289	Interface structure in heteroepitaxial CdTe on GaAs(100). <i>Surface Science</i> , 1986 , 168, 564-570	1.8	61
288	Misfit Strain Relaxation by Stacking Fault Generation in InGaIn Quantum Wells Grown on-m-Plane GaN. <i>Applied Physics Express</i> , 2009 , 2, 041002	2-4	60
287	Direct imaging of impurity-induced Raman scattering in GaN. <i>Applied Physics Letters</i> , 1996 , 69, 2650-2652	3-4	59
286	Engineered Schottky barrier diodes for the modification and control of Schottky barrier heights. <i>Journal of Applied Physics</i> , 1987 , 61, 5159-5169	2-5	57
285	Atomic motion on the surface of a cadmium telluride single crystal. <i>Nature</i> , 1981 , 290, 386-388	50-4	57
284	Structural and optical properties of nonpolar GaIn thin films. <i>Applied Physics Letters</i> , 2008 , 92, 171904	3-4	56
283	Resonant tunneling in GaAs/AlAs heterostructures grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 1985 , 46, 285-287	3-4	56
282	Synthesis and luminescence properties of ZnO nanostructures produced by the sol-gel method. <i>Journal of Crystal Growth</i> , 2008 , 310, 599-603	1-6	55
281	Low Stokes shift in thick and homogeneous InGaIn epilayers. <i>Applied Physics Letters</i> , 2002 , 80, 550-552	3-4	54
280	Control of quantum-confined Stark effect in InGaIn/GaN multiple quantum well active region by p-type layer for III-nitride-based visible light emitting diodes. <i>Applied Physics Letters</i> , 2008 , 92, 101113	3-4	53
279	Generation of misfit dislocations by basal-plane slip in InGaIn/GaN heterostructures. <i>Applied Physics Letters</i> , 2006 , 89, 201911	3-4	53
278	Dynamic observation of defect annealing in CdTe at lattice resolution. <i>Nature</i> , 1982 , 298, 127-131	50-4	52

277	Epitaxial BaTiO ₃ /MgO Structure Grown on GaAs(100) by Pulsed Laser Deposition*. <i>Japanese Journal of Applied Physics</i> , 1993 , 32, 4099-4102	1.4	51
276	Excimer-laser-induced crystallization of hydrogenated amorphous silicon. <i>Applied Physics Letters</i> , 1990 , 57, 2222-2224	3.4	51
275	Fault-free silicon at the silicon/sapphire interface. <i>Applied Physics Letters</i> , 1982 , 41, 371-373	3.4	51
274	Mapping electrostatic potential across an AlGaN/InGaN/AlGaN diode by electron holography. <i>Applied Physics Letters</i> , 2000 , 76, 3055-3057	3.4	50
273	High critical current densities in epitaxial YBa ₂ Cu ₃ O _{7-x} thin films on silicon-on-sapphire. <i>Applied Physics Letters</i> , 1991 , 58, 2432-2434	3.4	50
272	Effect of interface chemistry on the growth of ZnSe on the Si(100) surface. <i>Physical Review B</i> , 1992 , 45, 13400-13406	3.3	49
271	Fine structure of AlN/AlGaN superlattice grown by pulsed atomic-layer epitaxy for dislocation filtering. <i>Applied Physics Letters</i> , 2005 , 87, 211915	3.4	46
270	Demonstration of transverse-magnetic deep-ultraviolet stimulated emission from AlGaN multiple-quantum-well lasers grown on a sapphire substrate. <i>Applied Physics Letters</i> , 2015 , 106, 041115	3.4	45
269	Carrier localization and nonradiative recombination in yellow emitting InGaN quantum wells. <i>Applied Physics Letters</i> , 2010 , 96, 031906	3.4	44
268	Origins of unintentional incorporation of gallium in AlInN layers during epitaxial growth, part I: Growth of AlInN on AlN and effects of prior coating. <i>Journal of Crystal Growth</i> , 2014 , 388, 137-142	1.6	43
267	Lattice structure at ZnSe/GaAs heterojunction interfaces prepared by organometallic chemical vapor deposition. <i>Thin Solid Films</i> , 1983 , 104, 133-143	2.2	43
266	Growth of high-quality AlN layers on sapphire substrates at relatively low temperatures by metalorganic chemical vapor deposition. <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 1089-1095	1.3	42
265	Study of charge distribution across interfaces in GaN/InGaN/GaN single quantum wells using electron holography. <i>Journal of Applied Physics</i> , 2002 , 91, 9856	2.5	42
264	Determination of the atomic structure of inversion domain boundaries in InGaN by transmission electron microscopy. <i>Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties</i> , 1998 , 77, 273-286		42
263	Measurement of the piezoelectric field across strained InGaN/GaN layers by electron holography. <i>Solid State Communications</i> , 1999 , 111, 281-285	1.6	42
262	Comprehensive study of the electronic and optical behavior of highly degenerate p-type Mg-doped GaN and AlGaN. <i>Journal of Applied Physics</i> , 2015 , 117, 045710	2.5	41
261	Investigation of GaN-on-GaN vertical p-n diode with regrown p-GaN by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2018 , 113, 233502	3.4	41
260	Origins of unintentional incorporation of gallium in InAlN layers during epitaxial growth, part II: Effects of underlying layers and growth chamber conditions. <i>Journal of Crystal Growth</i> , 2014 , 388, 143-149	1.6	40

259	Bright, Crack-Free InGaN/GaN Light Emitters on Si(111). <i>Physica Status Solidi A</i> , 2002 , 192, 308-313		39
258	Determination by Electron Holography of the Electronic Charge Distribution at Threading Dislocations in Epitaxial GaN. <i>Physica Status Solidi A</i> , 2002 , 192, 407-411		38
257	Polychromatic light emission from single InGaN quantum wells grown on pyramidal GaN facets. <i>Applied Physics Letters</i> , 2005 , 87, 131911	3-4	38
256	Temperature dependence of the crystalline quality of AlN layer grown on sapphire substrates by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2015 , 414, 76-80	1.6	36
255	Localized states at InGaN/GaN quantum well interfaces. <i>Applied Physics Letters</i> , 1999 , 75, 3835-3837	3-4	36
254	Misfit dislocations in GaAs heteroepitaxy on (001) Si. <i>Journal of Crystal Growth</i> , 1990 , 106, 157-165	1.6	35
253	Summary Abstract: High resolution electron microscopy of CaF ₂ /silicon interfaces. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1986 , 4, 1121		34
252	Imaging of the silicon on sapphire interface by high-resolution transmission electron microscopy. <i>Applied Physics Letters</i> , 1981 , 38, 439-441	3-4	34
251	Misfit Dislocation Generation in InGaN Epilayers on Free-Standing GaN. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, L549-L551	1.4	33
250	Simple ion milling preparation of <111> tungsten tips. <i>Applied Physics Letters</i> , 1989 , 54, 1223-1225	3-4	33
249	High Voltage Vertical GaN p-n Diodes With Hydrogen-Plasma Based Guard Rings. <i>IEEE Electron Device Letters</i> , 2020 , 41, 127-130	4-4	33
248	Characterisation of dislocations, nanopipes and inversion domains in GaN by transmission electron microscopy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997 , 50, 76-81	3-1	32
247	Localization versus field effects in single InGaN quantum wells. <i>Applied Physics Letters</i> , 2004 , 84, 58-60	3-4	32
246	Electron Holography Studies of the Charge on Dislocations in GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2002 , 234, 924-930	1-3	32
245	Highly luminescent, high-indium-content InGaN film with uniform composition and full misfit-strain relaxation. <i>Applied Physics Letters</i> , 2013 , 103, 131101	3-4	31
244	100-nm thick single-phase wurtzite BAlN films with boron contents over 10%. <i>Physica Status Solidi (B): Basic Research</i> , 2017 , 254, 1600699	1-3	30
243	Sub-250 nm low-threshold deep-ultraviolet AlGaIn-based heterostructure laser employing HfO ₂ /SiO ₂ dielectric mirrors. <i>Applied Physics Letters</i> , 2013 , 103, 211103	3-4	30
242	Low-temperature growth of InGaN films over the entire composition range by MBE. <i>Journal of Crystal Growth</i> , 2015 , 425, 115-118	1.6	30

241	Growth of self-assembled GaN quantum dots via the vapor-liquid-solid mechanism. <i>Applied Physics Letters</i> , 2002 , 81, 3236-3238	3.4	30
240	Effects of heavy boron doping upon oxygen precipitation in Czochralski silicon. <i>Journal of Applied Physics</i> , 1988 , 64, 4454-4465	2.5	30
239	Native tellurium dioxide layer on cadmium telluride: A high-resolution electron microscopy study. <i>Applied Physics Letters</i> , 1981 , 39, 951-953	3.4	29
238	Compositional instability in InAlN/GaN lattice-matched epitaxy. <i>Applied Physics Letters</i> , 2012 , 100, 092103	3.4	28
237	Atomic arrangement at the Au-β-GaN interface in low-resistance contacts. <i>Applied Physics Letters</i> , 2004 , 85, 6143-6145	3.4	28
236	Effect of layer thickness on the electrostatic potential in InGaN quantum wells. <i>Applied Physics Letters</i> , 2004 , 85, 4651-4653	3.4	28
235	Microstructural properties of Eu-doped GaN luminescent powders. <i>Applied Physics Letters</i> , 2002 , 81, 1993-1995	3.4	28
234	Characterization of OMVPE-Grown AlGaInN Heterostructures. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 449, 509		28
233	Crystal orientation dependence of the electrical transport and lattice structure of zinc selenide films grown by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , 1985 , 58, 1548-1553	2.5	28
232	Growth of GaN on ZrB ₂ substrate by metal-organic vapor phase epitaxy. <i>Applied Surface Science</i> , 2003 , 216, 502-507	6.7	27
231	Polarity determination and atomic arrangements at a GaN/SiC interface using high-resolution image matching. <i>Applied Physics Letters</i> , 2000 , 76, 822-824	3.4	27
230	The effect of a Ga prelayer on the beginning of GaAs epitaxy on Si. <i>Journal of Applied Physics</i> , 1988 , 64, 3472-3475	2.5	27
229	Graded-thickness samples for molecular beam epitaxial growth studies of GaAs/Si heteroepitaxy. <i>Applied Physics Letters</i> , 1988 , 52, 1779-1781	3.4	27
228	High-resolution transmission electron microscopy of 60[dot] dislocations in si-GaAs. <i>Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties</i> , 1989 , 59, 1045-1058		26
227	Dislocation generation at the coalescence of aluminum nitride lateral epitaxy on shallow-grooved sapphire substrates. <i>Applied Physics Letters</i> , 2007 , 90, 221909	3.4	25
226	Structural and optical characterization of nonpolar GaN/AlN quantum wells. <i>Applied Physics Letters</i> , 2003 , 83, 653-655	3.4	25
225	Atomic arrangement at the AlN/ZrB ₂ interface. <i>Applied Physics Letters</i> , 2002 , 81, 3182-3184	3.4	25
224	Mapping the electrostatic potential across AlGaInN/GaN heterostructures using electron holography. <i>Applied Physics Letters</i> , 2007 , 90, 032101	3.4	24

223	Optoelectronic and microstructure attributes of epitaxial SrTiO ₃ on Si. <i>Journal of Applied Physics</i> , 2005 , 97, 014101	2.5	24
222	Sub 250 nm deep-UV AlGa _N /AlN distributed Bragg reflectors. <i>Applied Physics Letters</i> , 2017 , 110, 011105	3.4	23
221	Simulations, Practical Limitations, and Novel Growth Technology for InGa _N -Based Solar Cells. <i>IEEE Journal of Photovoltaics</i> , 2014 , 4, 601-606	3.7	23
220	Blue light emitting diodes grown on freestanding (11-20) a-plane GaN substrates. <i>Applied Physics Letters</i> , 2008 , 92, 011123	3.4	23
219	Role of the buffer layer thickness on the formation of basal plane stacking faults in a-plane GaN epitaxy on r-sapphire. <i>Applied Physics Letters</i> , 2008 , 93, 011901	3.4	23
218	Effect of internal electrostatic fields in InGa _N quantum wells on the properties of green light emitting diodes. <i>Applied Physics Letters</i> , 2007 , 91, 041915	3.4	23
217	Observation of coreless edge and mixed dislocations in Mg-doped Al _{0.03} Ga _{0.97} N. <i>Applied Physics Letters</i> , 2002 , 81, 4541-4543	3.4	23
216	Use of ZnSe as an interlayer for GaAs growth on Si. <i>Applied Physics Letters</i> , 1992 , 61, 195-197	3.4	23
215	Metal-Organic Hydride Vapor Phase Epitaxy of Al _x Ga _{1-x} N Films over Sapphire. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, L752-L754	1.4	22
214	Depth-resolved electron-excited nanoscale-luminescence spectroscopy studies of defects near GaN/InGa _N /GaN quantum wells. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999 , 17, 2545		22
213	Interface effects in amorphous silicon/nitride multilayers. <i>Journal of Non-Crystalline Solids</i> , 1985 , 77-78, 995-998	3.9	22
212	High-resolution lattice imaging of cadmium telluride. <i>Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties</i> , 1982 , 45, 693-711		22
211	Refractory In _{0.5} Ga _{0.5} N Solar Cells for High-Temperature Applications. <i>IEEE Journal of Photovoltaics</i> , 2017 , 7, 1646-1652	3.7	21
210	Microstructure of InGa _N Quantum Wells. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 482, 31		21
209	Defect formation near GaN surfaces and interfaces. <i>Physica B: Condensed Matter</i> , 1999 , 273-274, 70-74	2.8	21
208	Nanopipes and Inversion Domains in High-Quality GaN Epitaxial Layers. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 449, 405		21
207	Implantation-and etching-free high voltage vertical GaN p-n diodes terminated by plasma-hydrogenated p-GaN: revealing the role of thermal annealing. <i>Applied Physics Express</i> , 2019 , 12, 051015	2.4	20
206	Comparative Study on MOCVD Growth of a-Plane GaN Films on r-Plane Sapphire Substrates Using GaN, AlGa _N , and AlN Buffer Layers. <i>Journal of Electronic Materials</i> , 2009 , 38, 1938-1943	1.9	20

205	Atomic Arrangement at the AlN/Si(110) Interface. <i>Applied Physics Express</i> , 2008 , 1, 061104	2.4	20
204	Optical properties of highly luminescent zinc oxide tetrapod powders. <i>Applied Physics Letters</i> , 2007 , 91, 121905	3.4	20
203	Plasticity and optical properties of GaN under highly localized nanoindentation stress fields. <i>Journal of Applied Physics</i> , 2017 , 121, 125105	2.5	19
202	Time-resolved cathodoluminescence of Mg-doped GaN. <i>Applied Physics Letters</i> , 2008 , 93, 151901	3.4	19
201	Epitaxial growth of Al _x Ga _{1-x} N on Si(111) via a ZrB ₂ (0001) buffer layer. <i>Applied Physics Letters</i> , 2004 , 84, 3510-3512	3.4	19
200	Strain Relaxation Mechanisms in AlGa _N Epitaxy on AlN Templates. <i>Applied Physics Express</i> , 2010 , 3, 111003	4	18
199	Defect and stress control of AlGa _N for fabrication of high performance UV light emitters. <i>Physica Status Solidi A</i> , 2004 , 201, 2679-2685		18
198	A Comparison of Rutherford Backscattering Spectroscopy and X-Ray Diffraction to Determine the Composition of Thick InGa _N Epilayers. <i>Physica Status Solidi (B): Basic Research</i> , 2001 , 228, 41-44	1.3	18
197	High-Quality GaN heteroepitaxial films grown by metalorganic chemical vapor deposition. <i>Journal of Electronic Materials</i> , 1995 , 24, 257-261	1.9	18
196	Microscopic aspects of oxygen precipitation in silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1989 , 4, 11-17	3.1	18
195	Non-uniform Mg distribution in GaN epilayers grown on mesa structures for applications in GaN power electronics. <i>Applied Physics Letters</i> , 2019 , 114, 082102	3.4	17
194	The effect of InGa _N underlayers on the electronic and optical properties of InGa _N /GaN quantum wells. <i>Applied Physics Letters</i> , 2013 , 102, 041115	3.4	17
193	Optimization of growth conditions for InGaAs/InAlAs/InP quantum cascade lasers by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2011 , 316, 75-80	1.6	17
192	In-plane polarization of GaN-based heterostructures with arbitrary crystal orientation. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010 , 207, 2226-2232	1.6	17
191	Gallium-nitride-based devices on silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 1940-1949		17
190	Microscopic correlation of redshifted luminescence and surface defects in thick In _x Ga _{1-x} N layers. <i>Applied Physics Letters</i> , 2002 , 80, 3524-3526	3.4	17
189	Critical thickness determination of InAs, InP and GaP on GaAs by X-ray interference effect and transmission electron microscopy. <i>Journal of Crystal Growth</i> , 1993 , 131, 465-469	1.6	17
188	Outgrowths in C+ Thin Films of LiNbO ₃ on Al ₂ O ₃ -c. <i>Materials Research Society Symposia Proceedings</i> , 1994 , 341, 289		16

187	HgTe/CdTe superlattices grown on lattice-mismatched GaAs substrates. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1986 , 4, 1306		16
186	Crystal structure and composition of BAlN thin films: Effect of boron concentration in the gas flow. <i>Journal of Crystal Growth</i> , 2017 , 475, 334-340	1.6	15
185	Onset of surface stimulated emission at 260 nm from AlGaIn multiple quantum wells. <i>Applied Physics Letters</i> , 2015 , 107, 241109	3-4	15
184	Correlation of spectral luminescence with threading dislocations in green-light-emitting InGaIn quantum wells. <i>Applied Physics Letters</i> , 2007 , 90, 231901	3-4	15
183	Spatial variation of luminescence from AlGaIn grown by facet controlled epitaxial lateral overgrowth. <i>Applied Physics Letters</i> , 2004 , 85, 3417-3419	3-4	15
182	Spatial variation of luminescence in thick GaN films. <i>Applied Physics Letters</i> , 2001 , 78, 1222-1224	3-4	15
181	Interface properties of n-ZnSe/Ge heterojunctions grown by organometallic chemical vapor deposition. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1983 , 1, 656		15
180	Structure of Thermally-Induced Microdefects in Czochralski Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1983 , 31, 153		15
179	Origin of high hole concentrations in Mg-doped GaN films. <i>Physica Status Solidi (B): Basic Research</i> , 2017 , 254, 1600668	1-3	14
178	A review of the synthesis of reduced defect density In _x Ga _{1-x} N for all indium compositions. <i>Solid-State Electronics</i> , 2017 , 136, 3-11	1-7	14
177	Ammonothermal growth of high-quality GaN crystals on HVPE template seeds. <i>Journal of Crystal Growth</i> , 2011 , 318, 1030-1033	1.6	14
176	Effect of misfit dislocations on luminescence in m-plane InGaIn quantum wells. <i>Applied Physics Letters</i> , 2011 , 98, 261914	3-4	14
175	Mechanism of H ₂ pre-annealing on the growth of GaN on sapphire by MOVPE. <i>Applied Surface Science</i> , 2003 , 216, 585-589	6.7	14
174	Initial Stages of GaAs Epitaxy on Si. <i>Materials Research Society Symposia Proceedings</i> , 1988 , 116, 33		14
173	Optically pumped vertical-cavity surface-emitting laser at 374.9 nm with an electrically conducting n-type distributed Bragg reflector. <i>Applied Physics Express</i> , 2016 , 9, 111002	2.4	14
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